

±30V, 11A&-11A, 21mΩ&20mΩ N And P-channel Power Trench MOSFET JMTG200C03D

Features

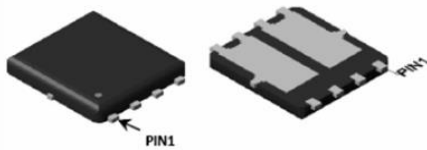
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED
- 100% ΔV_{ds} TESTED
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

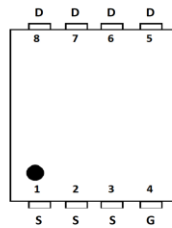
Parameters	N	P	Unit
V_{DSS}	30	-30	V
$V_{GS(th)_{Typ}}$	1.7	-1.7	V
$I_D(@V_{GS}=10V)$	11	-11	A
$R_{DS(ON)_{Typ}}(@V_{GS}=10V)$	15	15	mΩ
$R_{DS(ON)_{Typ}}(@V_{GS}=4.5V)$	21	20	mΩ



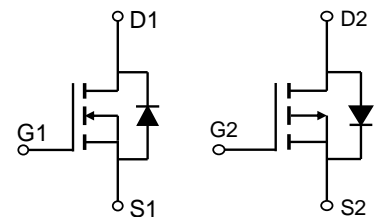
Top View

Bottom View

PDFN5x6-8L-D



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTG200C03D	G200C03D	1	Tape&Reel	PDFN5x6-8L-D	5000	50000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value-N	Value-P	Unit
V_{DS}	Drain-to-Source Voltage	30	-30	V
V_{GS}	Gate-to-Source Voltage	±20		V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	11	-11
		$T_C = 100^\circ\text{C}$	8	-8
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4		A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	15	33	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	69	69
		$T_C = 100^\circ\text{C}$	28	28
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150		°C

Thermal Characteristics

Symbol	Parameter	Max		Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	58	57	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.8	1.8	

Electrical Characteristics-N($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.2	1.7	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}, I_D = 5\text{A}$	-	15	17	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 3\text{A}$	-	21	28	$\text{m}\Omega$
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	1.8	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 15\text{V}, f = 1\text{MHz}$	-	481	-	pF
C_{oss}	Output Capacitance		-	71	-	pF
C_{rss}	Reverse Transfer Capacitance		-	54	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 15\text{V}, I_D = 5\text{A}$	-	10	-	nC
Q_{gs}	Gate Source Charge		-	1.8	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	2.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 15\text{V}$ $I_D = 5\text{A}, R_{GEN} = 2.7\Omega$	-	5	-	ns
t_r	Turn-On Rise Time		-	28	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	15	-	ns
t_f	Turn-Off Fall Time		-	2	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	11	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	45	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 5\text{A}$	-		1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 5\text{A}, di/dt = 100\text{A/us}$	-	8	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	2.3	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J=25^\circ\text{C}$, $V_{DD}=15\text{V}$, $V_G=10\text{V}$, $R_G=25\text{ohm}$, $L=0.5\text{mH}$, $I_{AS}=7.7\text{A}$, $V_{DD}=0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

**Electrical Characteristics-P** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}$, $V_{GS} = 0\text{V}$	-	-	-1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250\mu\text{A}$	-1.2	-1.7	-2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁵⁾	$V_{GS} = -10\text{V}$, $I_D = -5\text{A}$	-	15	21	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}$, $I_D = -3\text{A}$	-	20	32	$\text{m}\Omega$
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	12	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = -15\text{V}$, $f = 1\text{MHz}$	-	1290	-	pF
C_{oss}	Output Capacitance		-	169	-	pF
C_{rss}	Reverse Transfer Capacitance		-	131	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to -4.5V $V_{DS} = -15\text{V}$, $I_D = -5\text{A}$	-	24	-	nC
Q_{gs}	Gate Source Charge		-	4	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = -10\text{V}$, $V_{DD} = -15\text{V}$ $I_D = -3\text{A}$, $R_{GEN} = 2.7\Omega$	-	5	-	ns
t_r	Turn-On Rise Time		-	22	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	61	-	ns
t_f	Turn-Off Fall Time		-	55	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	-4	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	-14	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = -5\text{A}$	-		-1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = -5\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$	-	12	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	4.2	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = -15\text{V}$, $V_G = -10\text{V}$, $R_G = 250\text{ohm}$, $L = 0.5\text{mH}$, $I_{AS} = -11.48\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB.
4. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
5. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics-N

Figure 1: Power De-rating

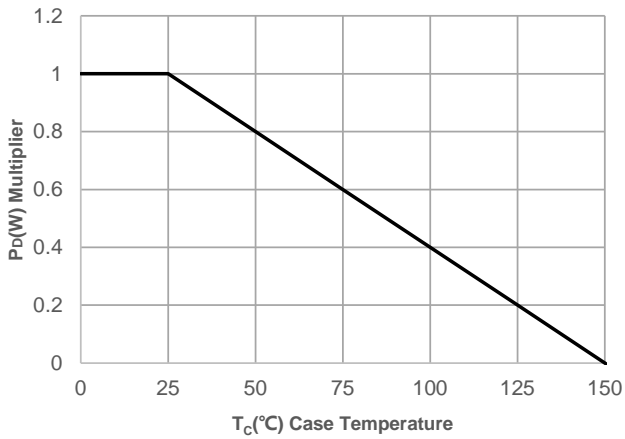


Figure 2: Current De-rating

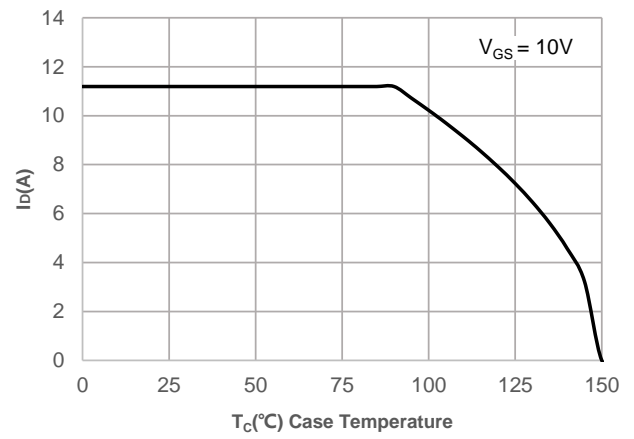


Figure 3: Normalized Maximum Transient Thermal Impedance

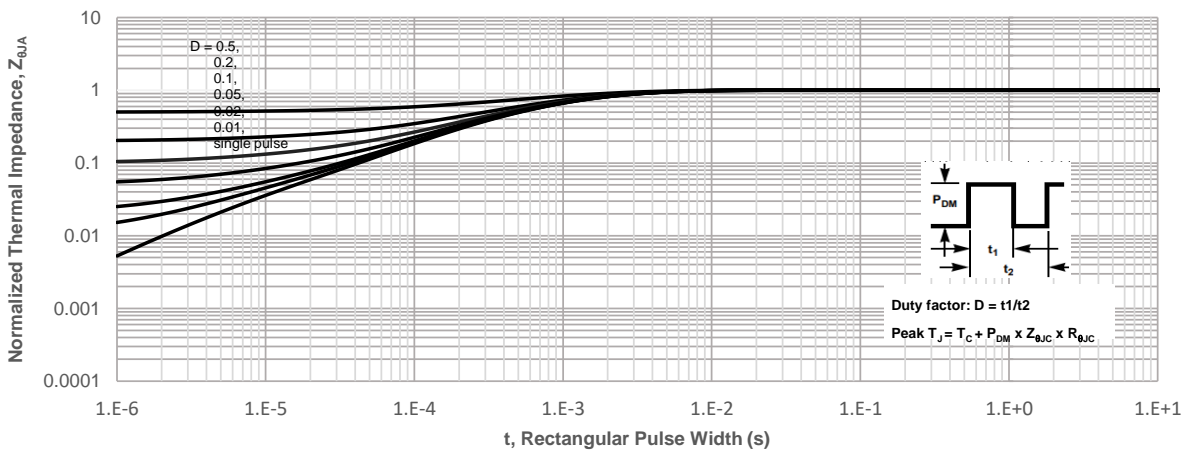
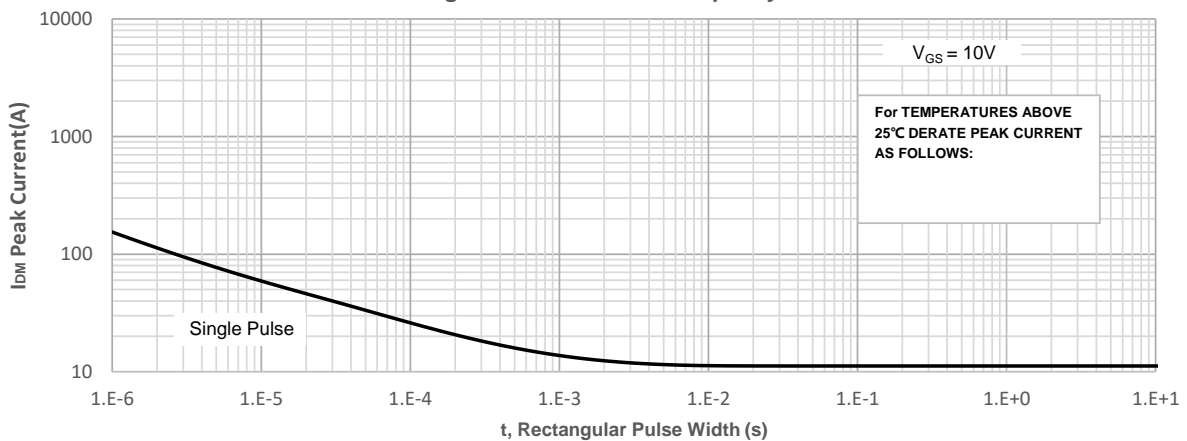
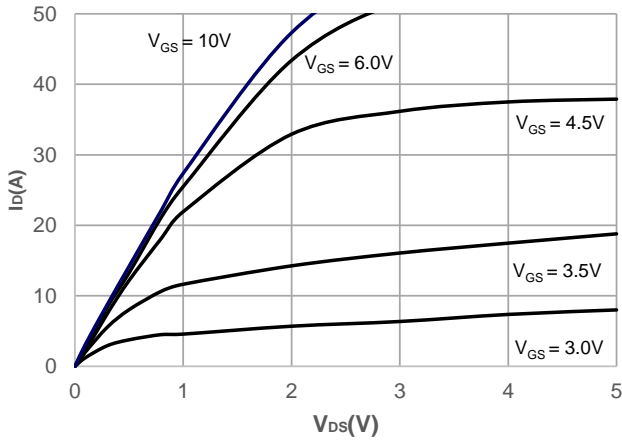
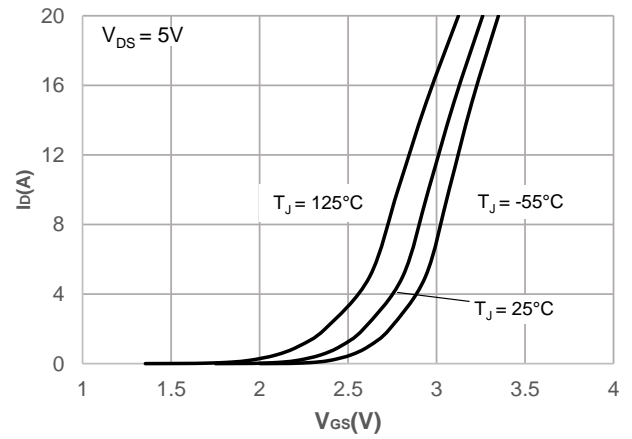
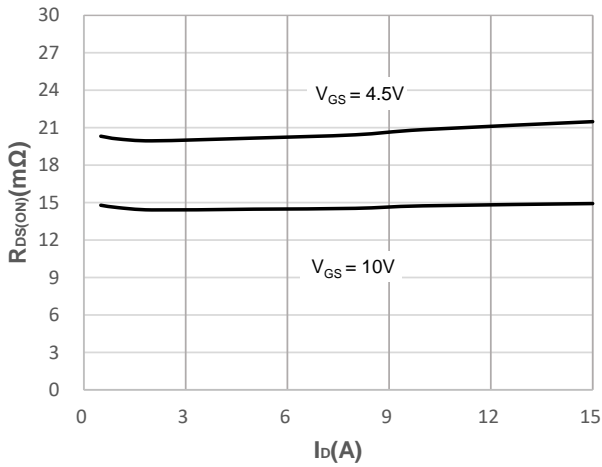
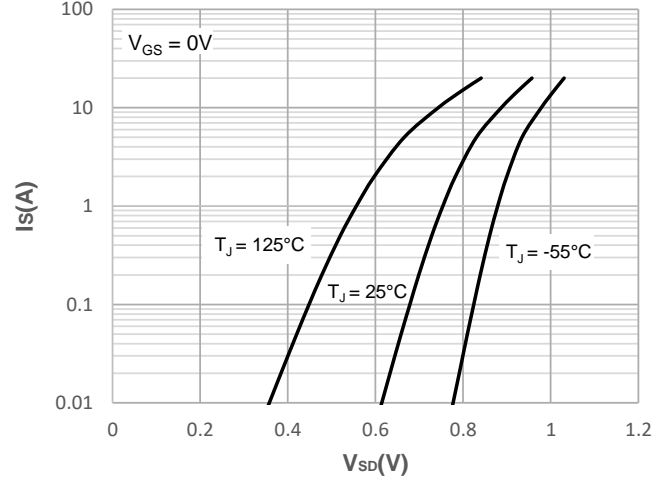
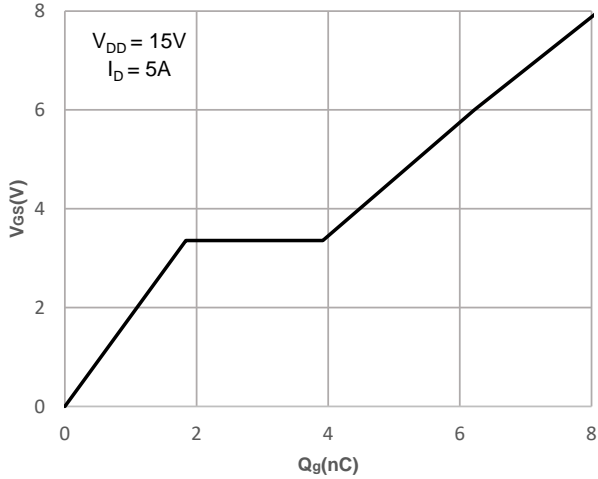
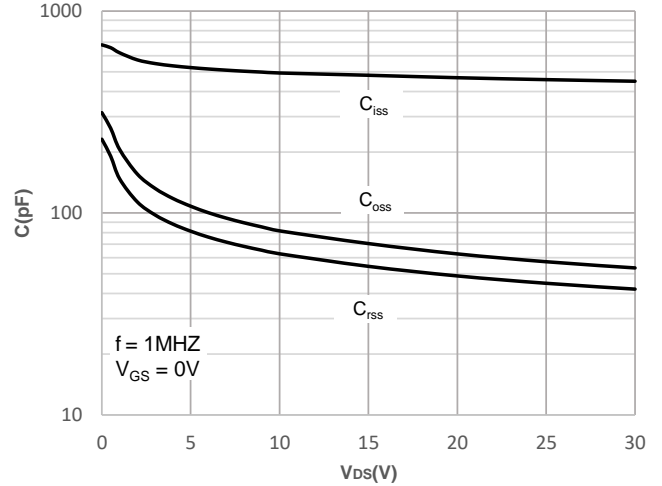


Figure 4: Peak Current Capacity



Typical Performance Characteristics-N

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics-N

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

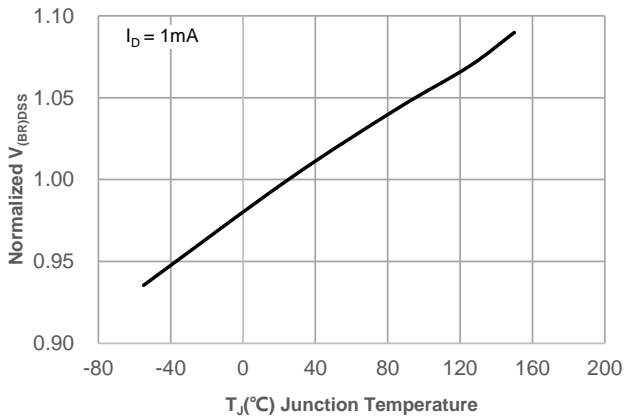


Figure 12: Normalized on Resistance vs. Junction Temperature

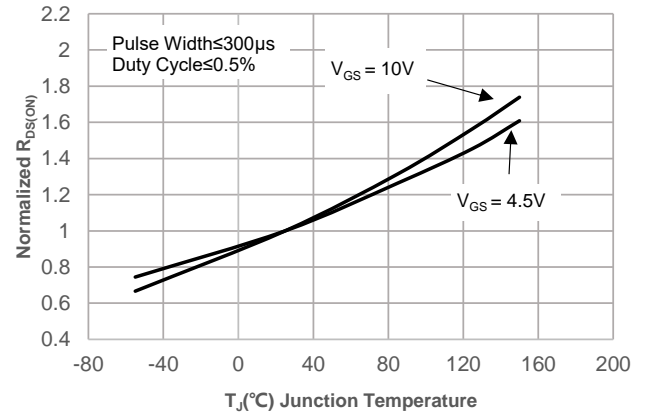


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

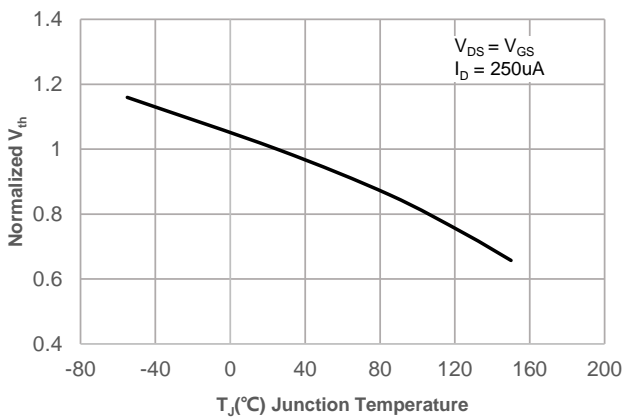


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

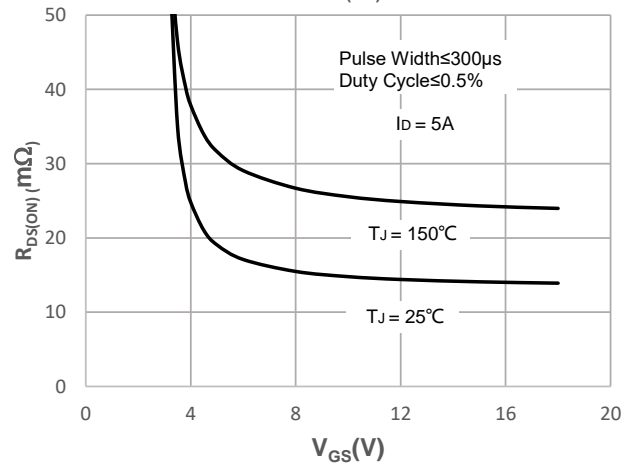
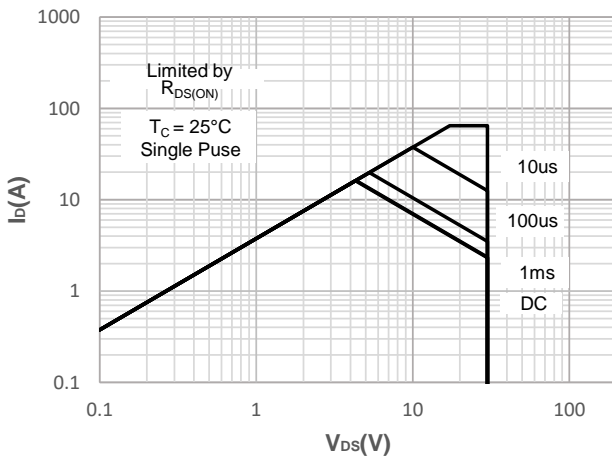


Figure 15: Maximum Safe Operating Area



Typical Performance Characteristics-P

Figure 1: Power De-rating

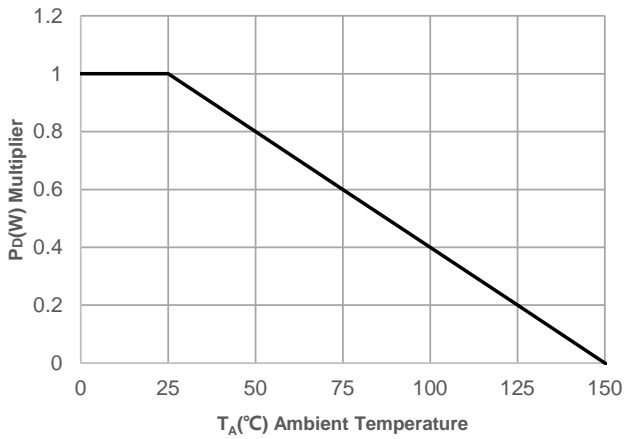


Figure 2: Current De-rating

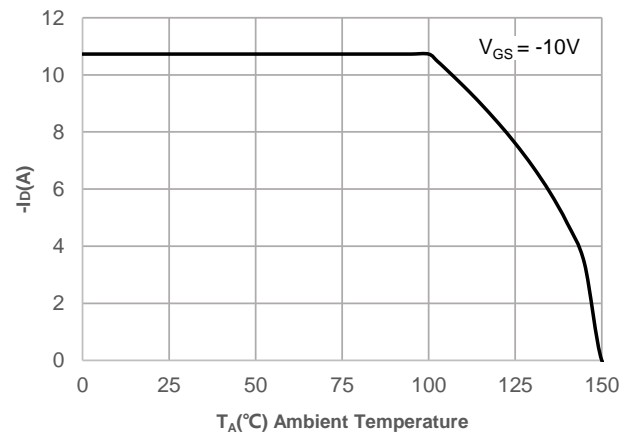


Figure 3: Normalized Maximum Transient Thermal Impedance

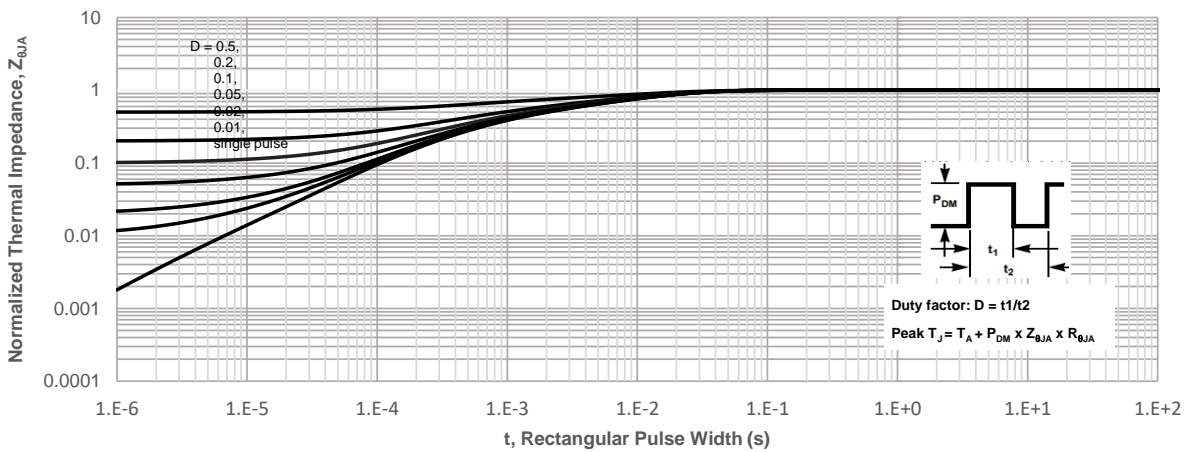
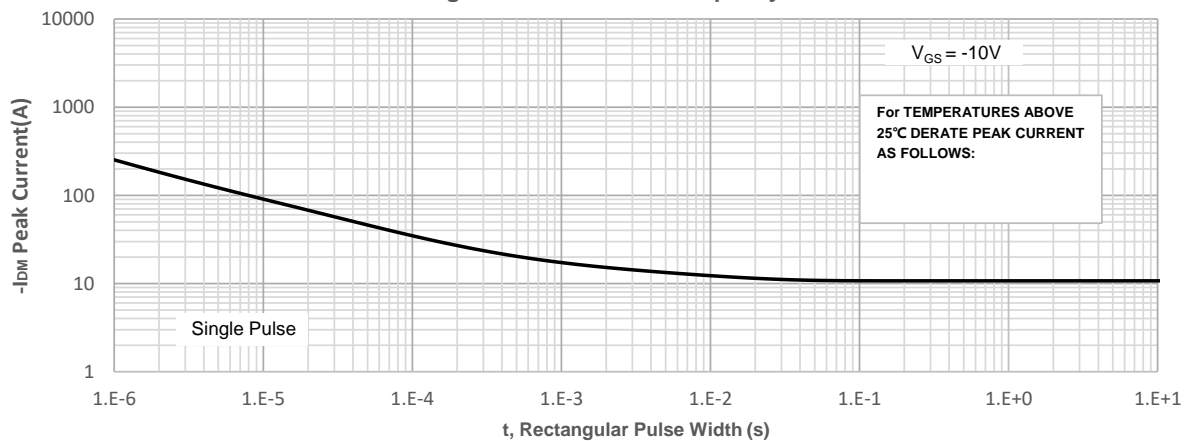
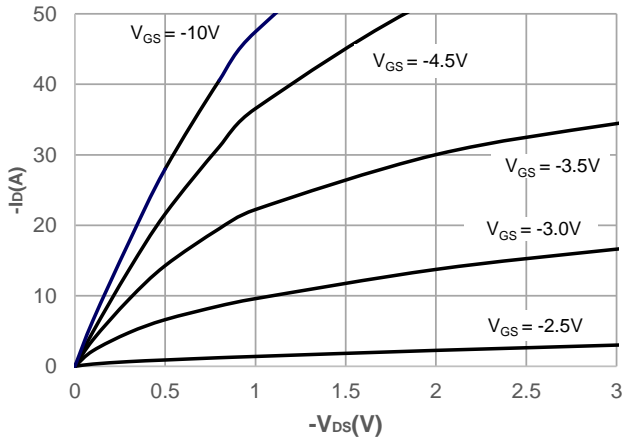
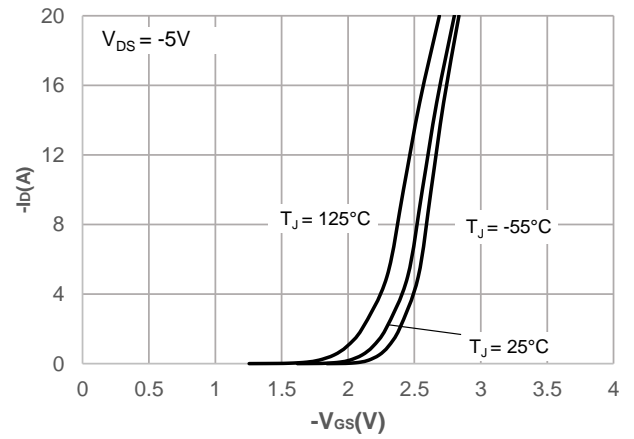
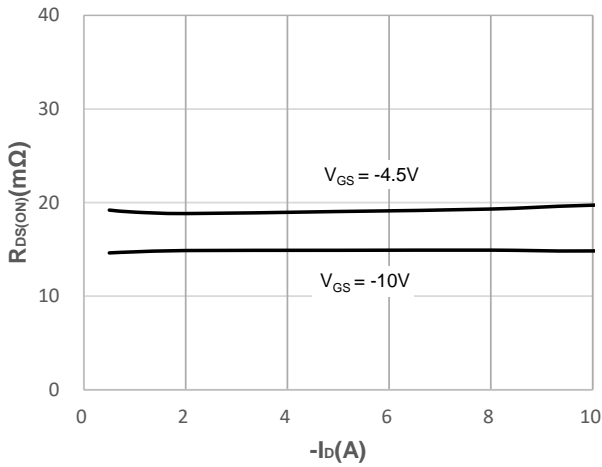
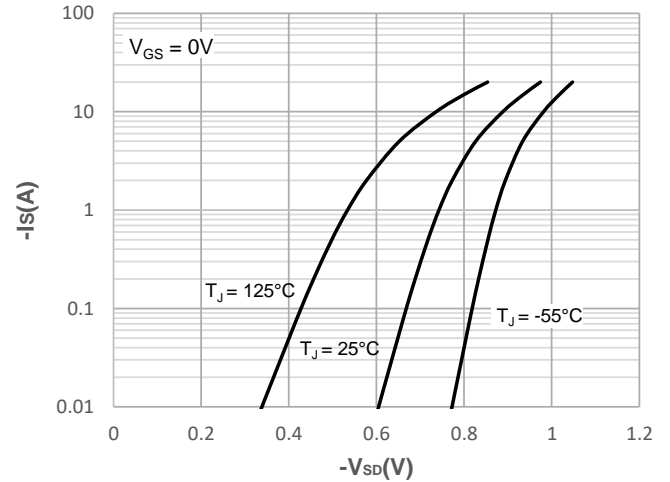
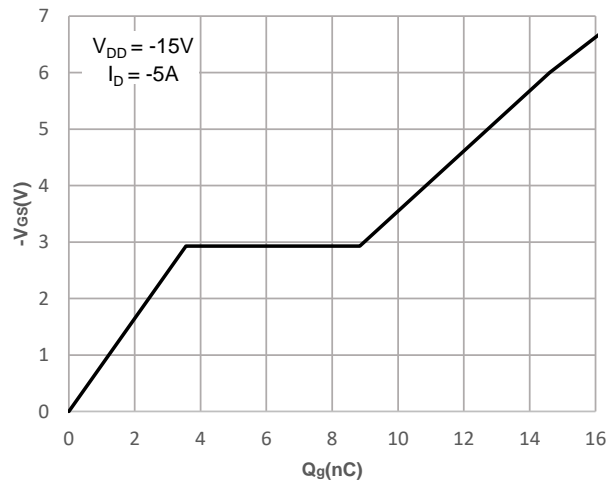
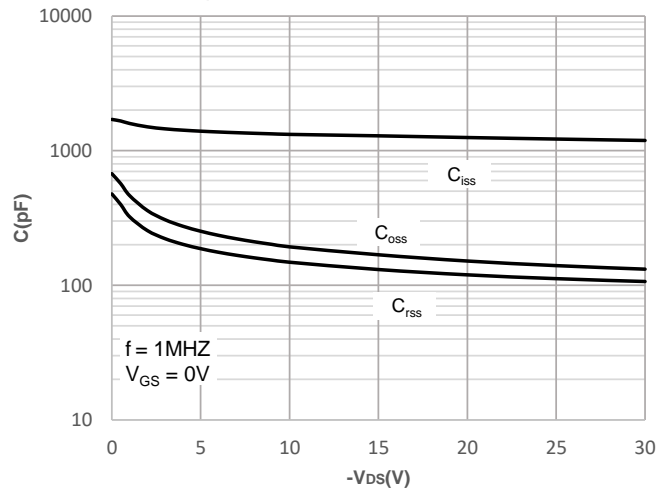


Figure 4: Peak Current Capacity



Typical Performance Characteristics-P

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics-P

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

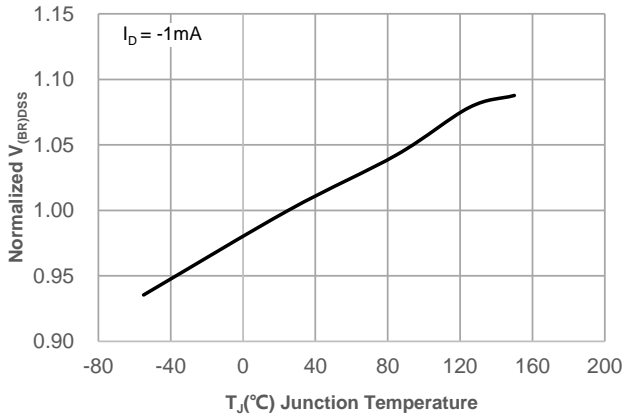


Figure 12: Normalized on Resistance vs. Junction Temperature

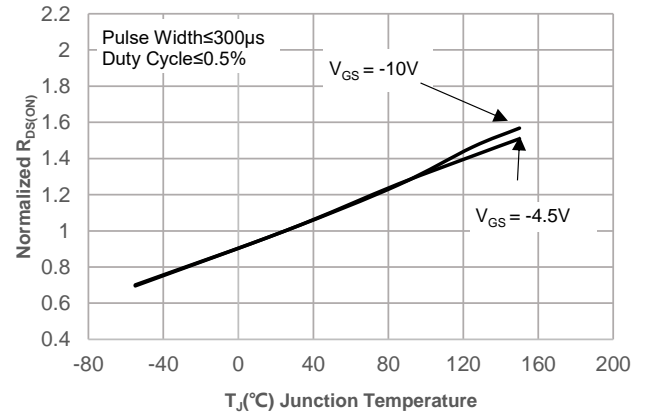


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

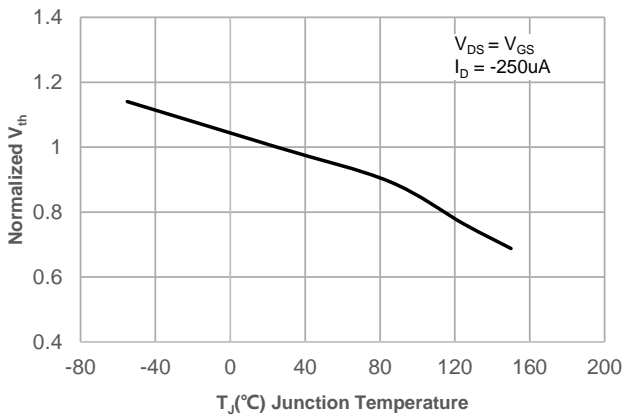


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

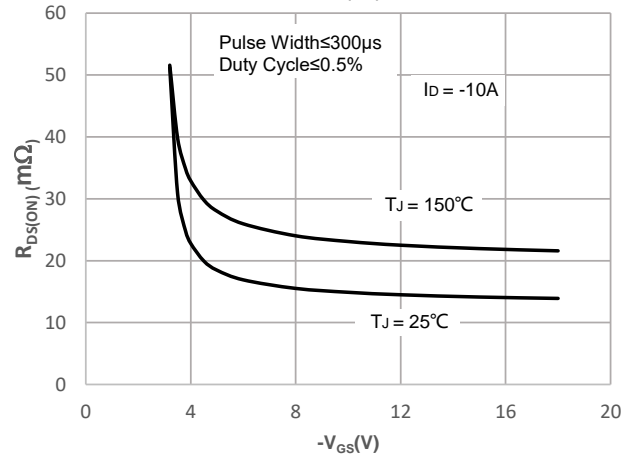
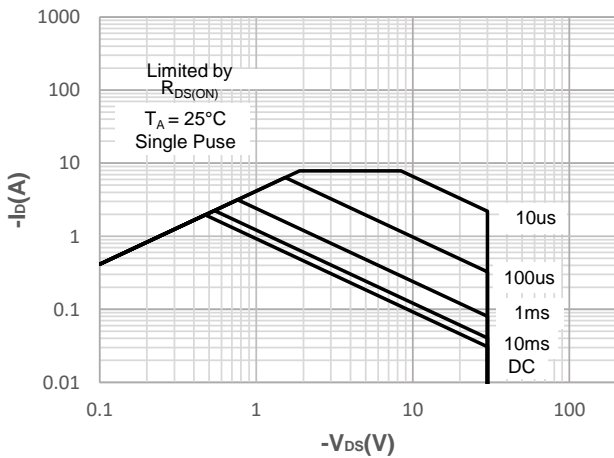
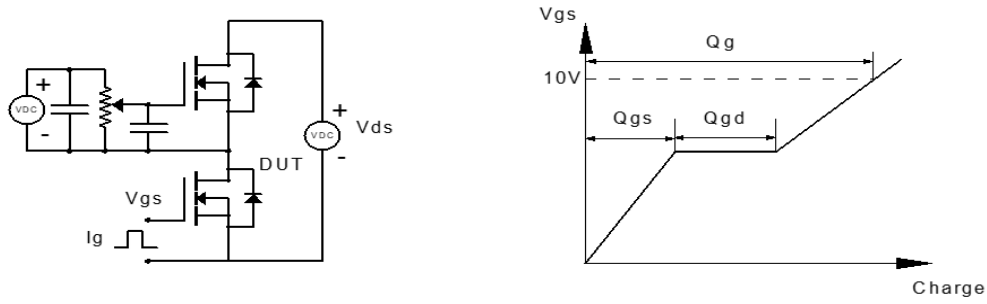
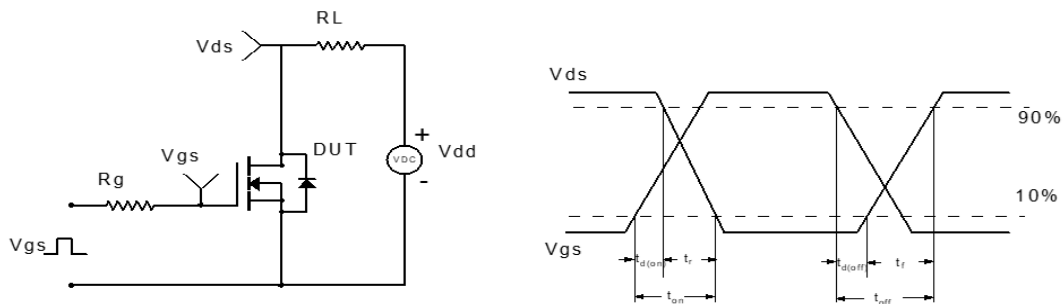
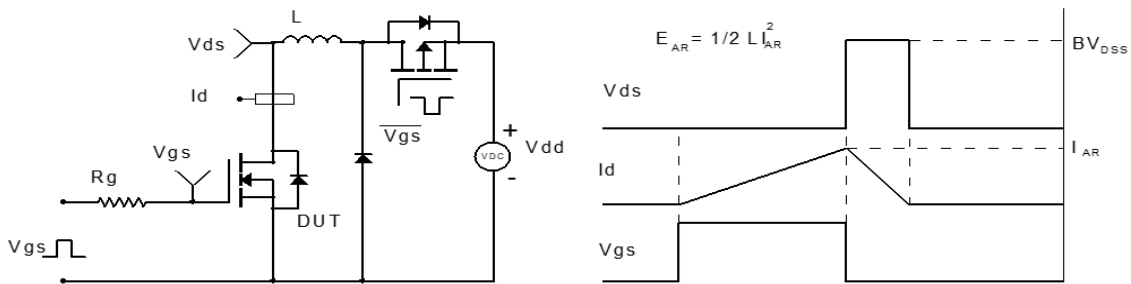
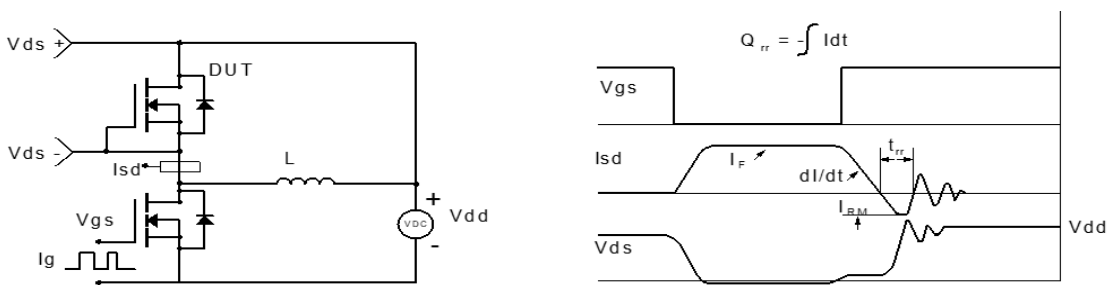


Figure 15: Maximum Safe Operating Area



Test Circuit-N

Figure 1: Gate Charge Test Circuit & Waveform

Figure 2: Resistive Switching Test Circuit & Waveform

Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

Figure 4: Diode Recovery Test Circuit & Waveform


Test Circuit-P

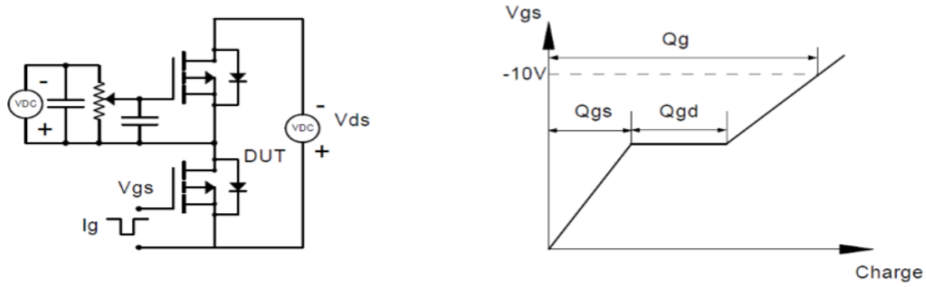


Figure 1: Gate Charge Test Circuit & Waveform

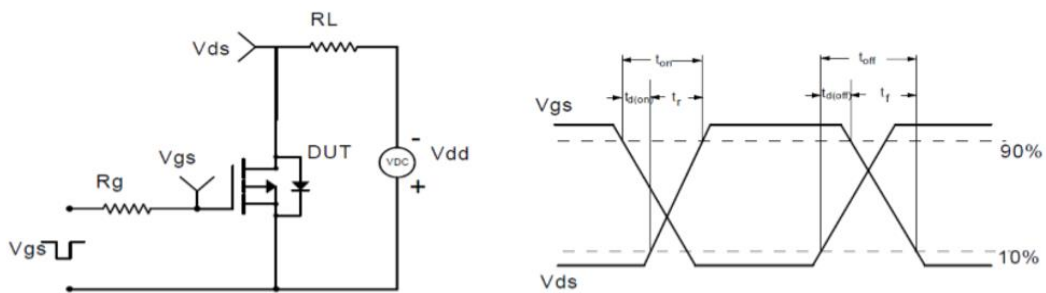


Figure 2: Resistive Switching Test Circuit & Waveform

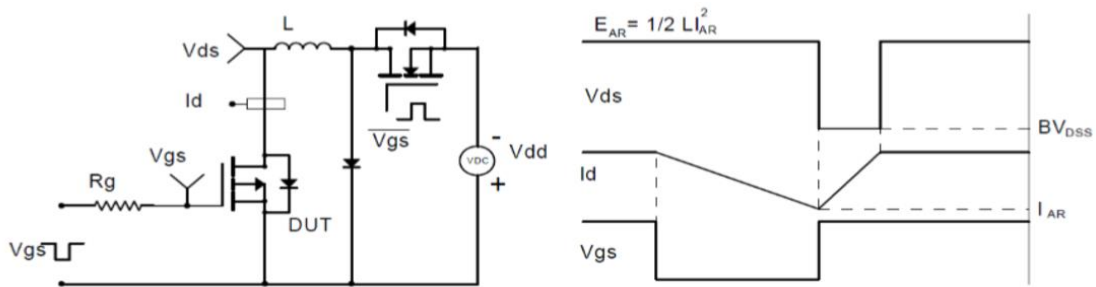


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

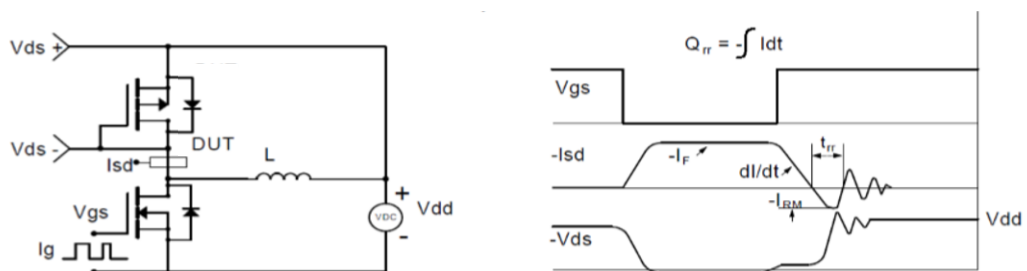
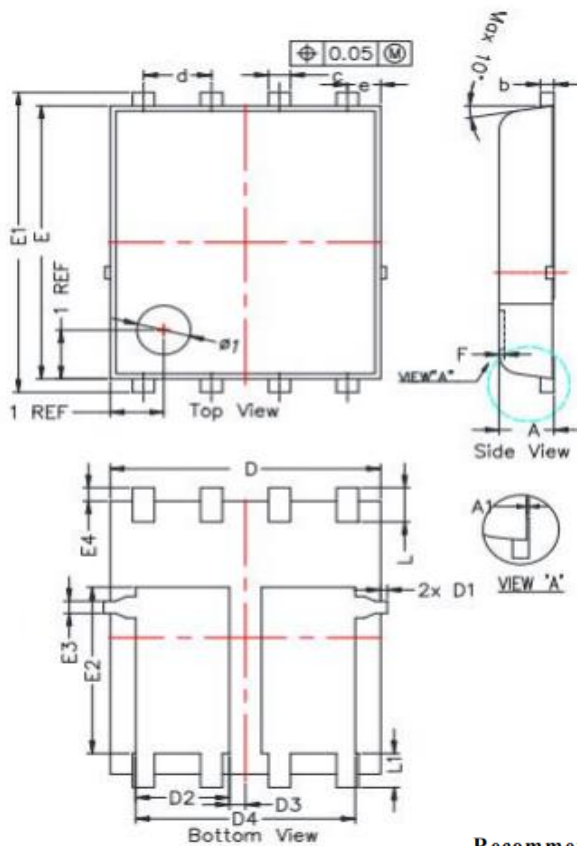
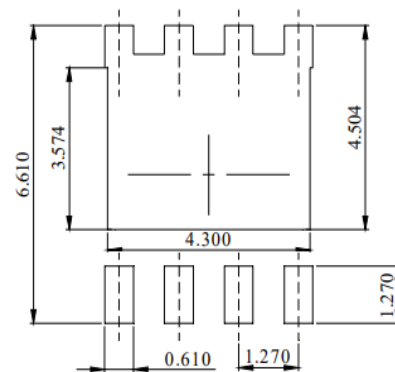


Figure 4: Diode Recovery Test Circuit & Waveform



Package Mechanical Data-PDFN5x6-8L-D


SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
* A	0.900	1.000	1.100	0.035	0.039	0.043
A1	0.000	---	0.050	0.000	---	0.002
b	0.246	0.254	0.312	0.010	0.010	0.012
* c	0.310	0.410	0.510	0.012	0.016	0.020
d	1.27 BSC			0.050 BSC		
* D	4.950	5.050	5.150	0.195	0.199	0.203
*D1	---	---	0.125	---	---	0.005
*D2	1.650	1.750	1.850	0.065	0.069	0.073
D3	0.200	0.300	0.400	0.008	0.012	0.016
D4	4.000	4.100	4.200	0.157	0.161	0.165
e	0.62 BSC			0.024 BSC		
* E	5.500	5.600	5.700	0.217	0.220	0.224
* E1	6.050	6.150	6.250	0.238	0.242	0.246
E2	3.310	3.410	3.510	0.130	0.134	0.138
E3	0.150	0.250	0.350	0.006	0.010	0.014
* E4	0.175	0.275	0.375	0.007	0.011	0.015
F	-	-	0.100	-	-	0.004
* L	0.500	0.600	0.700	0.02	0.02	0.03
L1	0.600	0.700	0.800	0.02	0.03	0.03

Recommended Soldering Footprint


DIMENSIONS: MILLIMETERS

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